

Ferro-Electric RAM

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Abstract: *Ferroelectric RAM (FRAM) is a promising non-volatile memory technology that combines the advantages of both DRAM and Flash memory. FRAM offers fast read and write speeds, low power consumption, and high endurance, making it suitable for a wide range of applications. It stores data by utilizing the ferroelectric properties of certain materials, which can retain their polarization even when the power is off. This allows FRAM to offer high-speed operation with low power consumption, making it ideal for use in IoT devices, smart cards, and automotive systems*

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